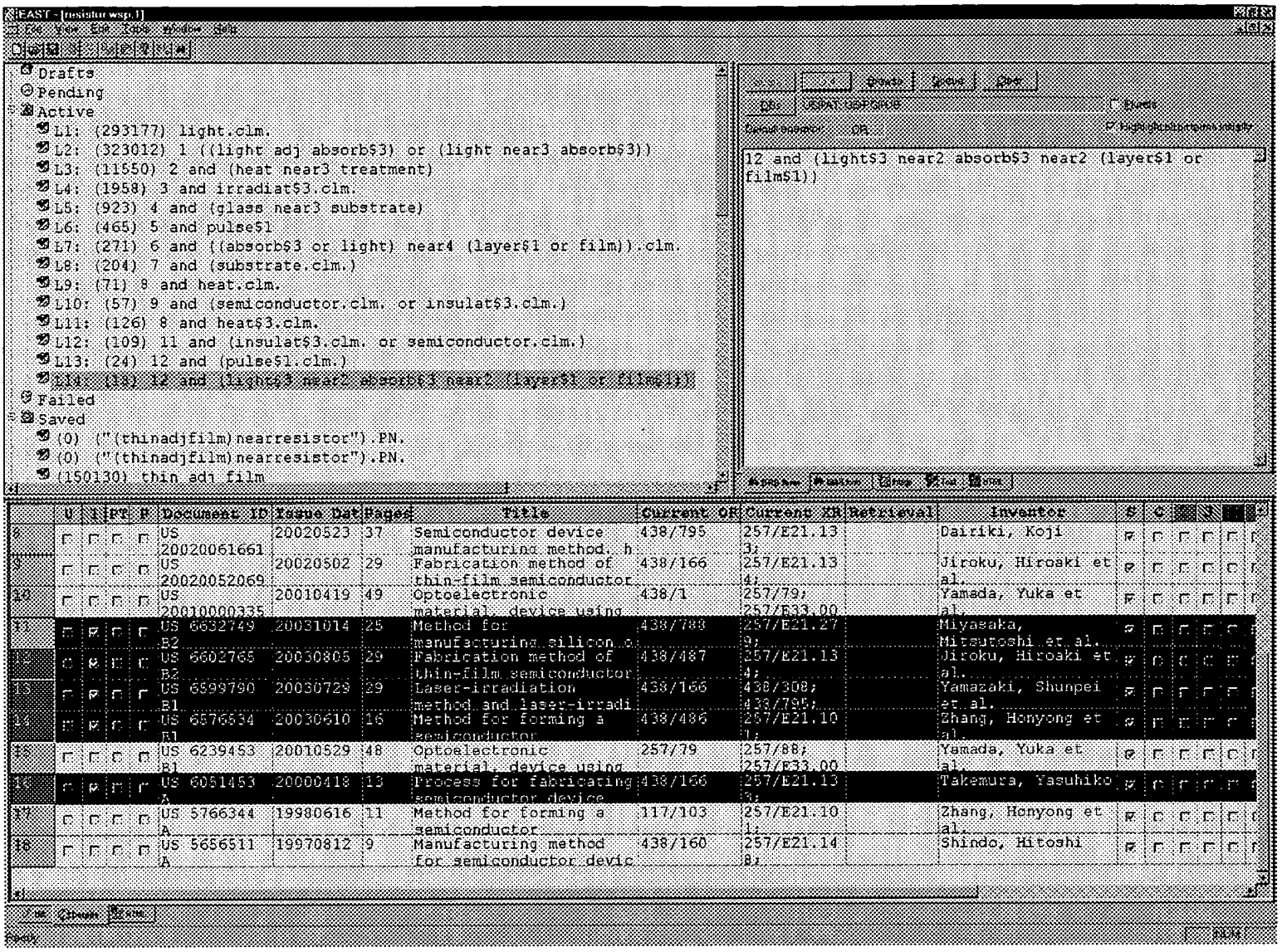

EAST - [resistor.wsp.1]
File View Edit Tools Window Help
Drafts
Pending
Active
L1: (293177) light.clm.
L2: (323012) 1 ((light adj absorb$3) or (light near3 absorb$3))
L3: (11550) 2 and (heat near3 treatment)
L4: (1958) 3 and irradiat$3.clm.
L5: (923) 4 and (glass near3 substrate)
L6: (465) 5 and pulse$1
L7: (271) 6 and ((absorb$3 or light) near4 (layer$1 or film)).clm.
L8: (204) 7 and (substrate.clm.)
L9: (71) 8 and heat.clm.
L10: (57) 9 and (semiconductor.clm. or insulat$3.clm.)
L11: (126) 8 and heat$3.clm.
L12: (109) 11 and (insulat$3.clm. or semiconductor.clm.)
L13: (24) 12 and (pulse$1.clm.)
L14: (18) 12 and (light$3 near2 absorb$3 near2 (layer$1 or film$1))
Failed
Saved
(0) ("(thinadjfilm)nearresistor").PN.
(0) ("(thinadjfilm)nearresistor").PN.
(150130) thin adj film
USPAT; USPGPUB
OR
12 and (light$3 near2 absorb$3 near2 (layer$1 or film$1))

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C
6					US 20020061661	20020523	37	Semiconductor device manufacturing method, h	438/795	257/E21.133;		Dairiki, Koji		
9					US 20020052069	20020502	29	Fabrication method of thin-film semiconductor	438/166	257/E21.134;		Jiroku, Hiroaki et al.		
10					US 20010000335	20010419	49	Optoelectronic material, device using	438/1	257/79; 257/E33.00		Yamada, Yuka et al.		
11					US 6632749 B2	20031014	25	Method for manufacturing silicon o	438/788	257/E21.279;		Miyasaka, Mitsutoshi et al.		
12					US 6602765 B2	20030805	29	Fabrication method of thin-film semiconductor	438/487	257/E21.134;		Jiroku, Hiroaki et al.		
13					US 6599790 B1	20030729	29	Laser-irradiation method and laser-irradi	438/166	438/308; 438/795;		Yamazaki, Shunpei et al.		
14					US 6576534 B1	20030610	16	Method for forming a semiconductor	438/486	257/E21.101;		Zhang, Hongyong et al.		
15					US 6239453 B1	20010529	48	Optoelectronic material, device using	257/79	257/88; 257/E33.00		Yamada, Yuka et al.		
16					US 6051453 A	20000418	13	Process for fabricating semiconductor device	438/166	257/E21.133;		Takemura, Yasuhiko		
17					US 5766344 A	19980616	11	Method for forming a semiconductor	117/103	257/E21.101;		Zhang, Hongyong et al.		
18					US 5656511 A	19970812	9	Manufacturing method for semiconductor devic	438/160	257/E21.148;		Shindo, Hitoshi		

Ready
NUM